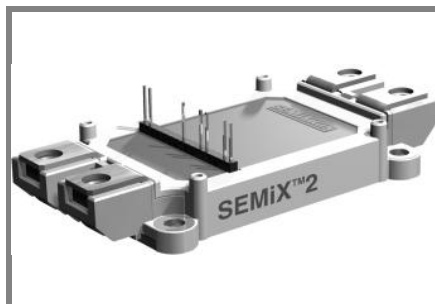


SEMiX 302GB126HD ...



SEMiX® 2

Trench IGBT Modules

SEMiX 302GB126HD

SEMiX 302GAL126HD

SEMiX 302GAR126HD

Target Data

Features

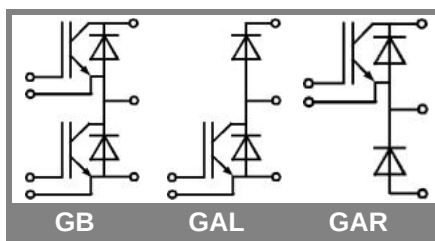
- Homogeneous Si
- Trench = Trenchgate technology
- $V_{CE(sat)}$ with positive temperature coefficient
- High short circuit capability

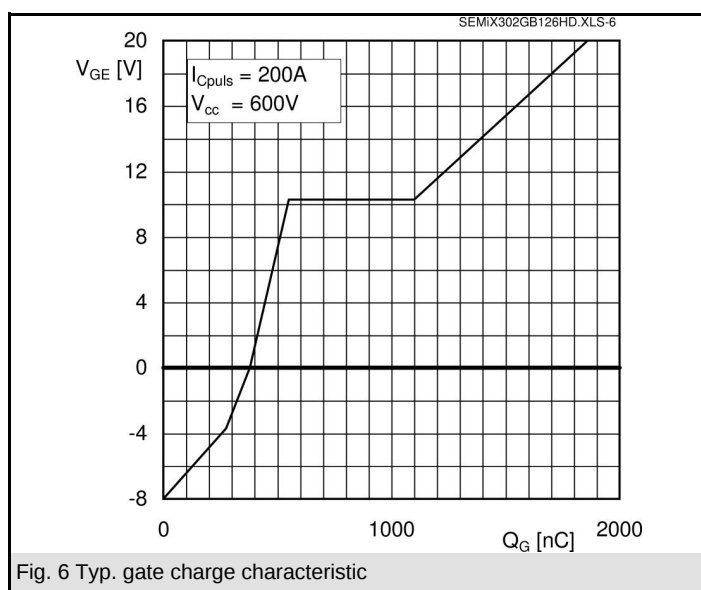
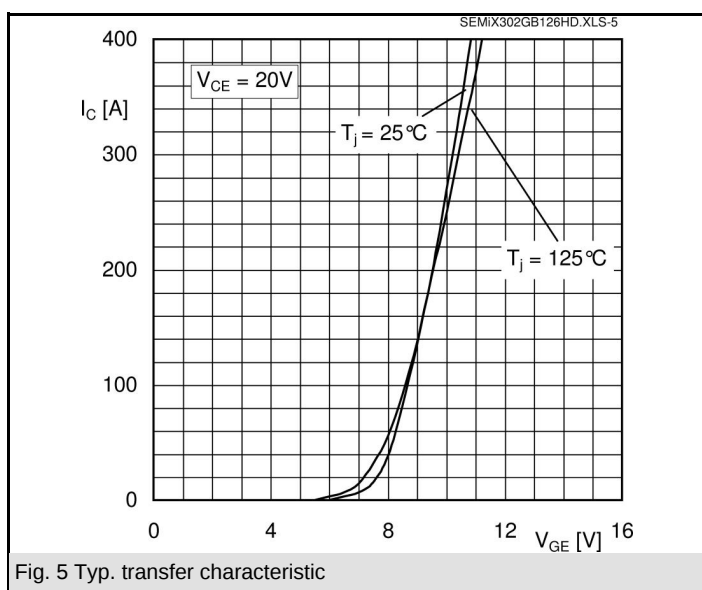
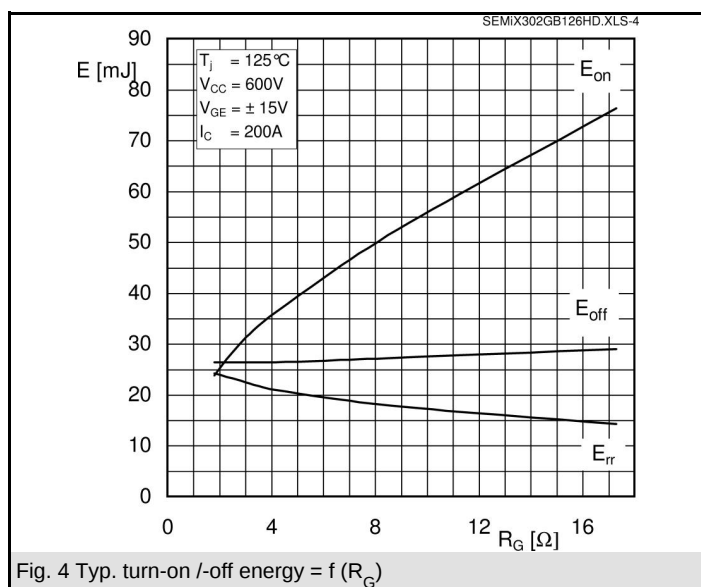
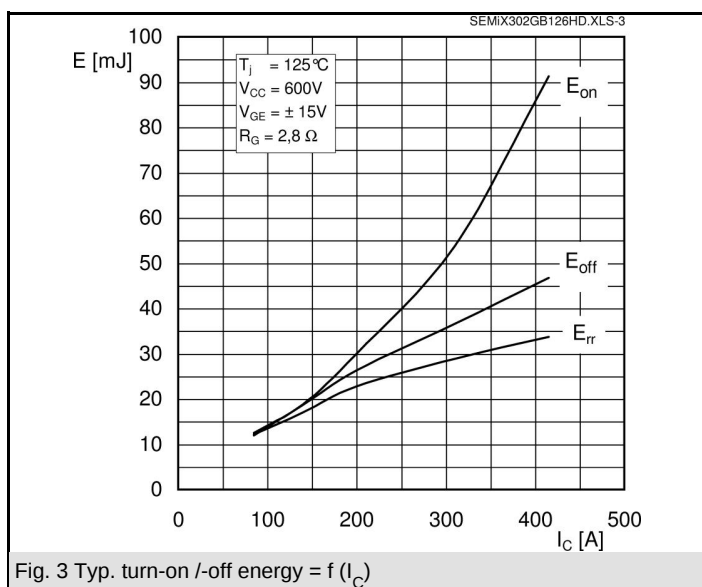
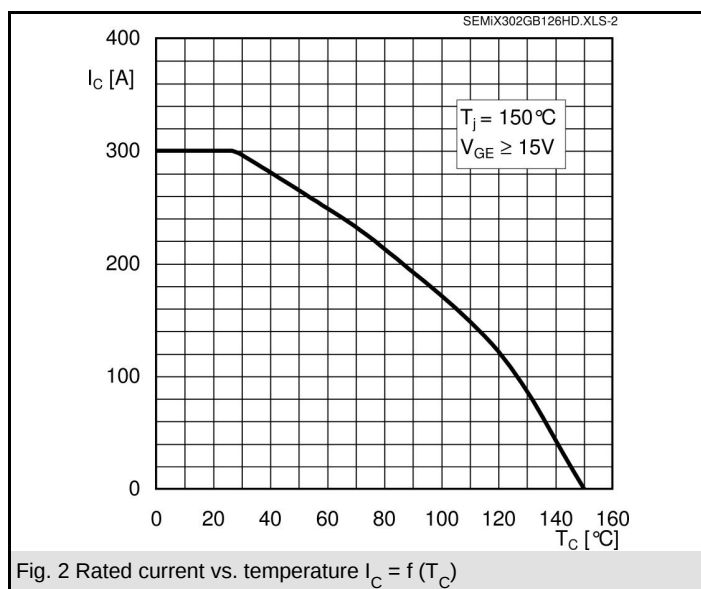
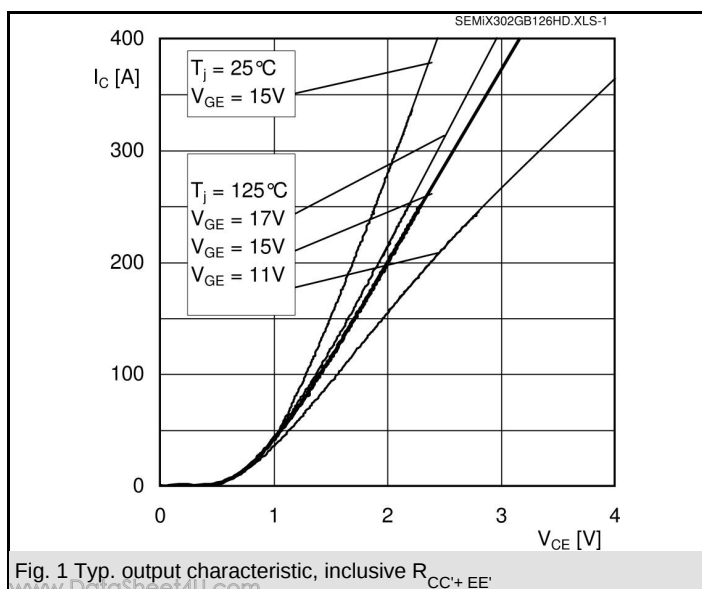
Typical Applications

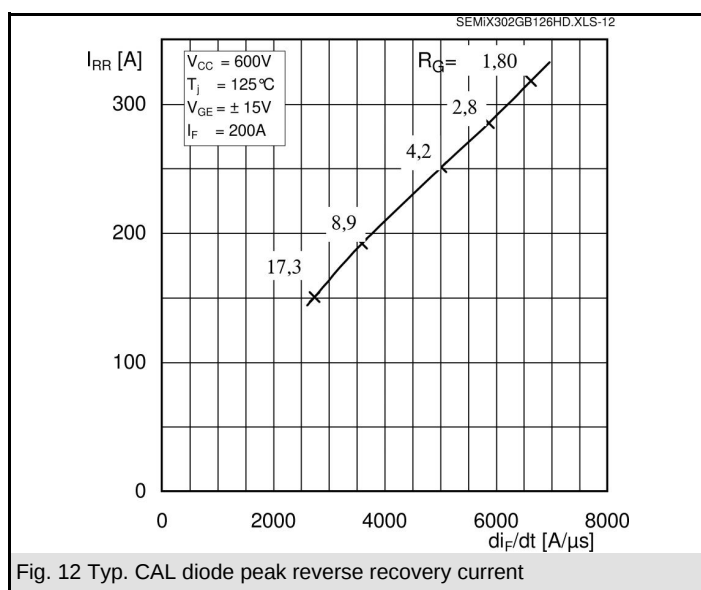
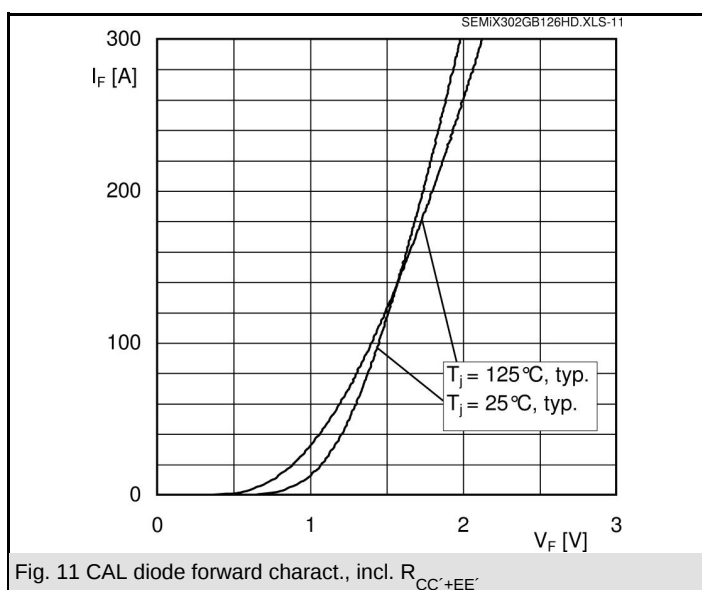
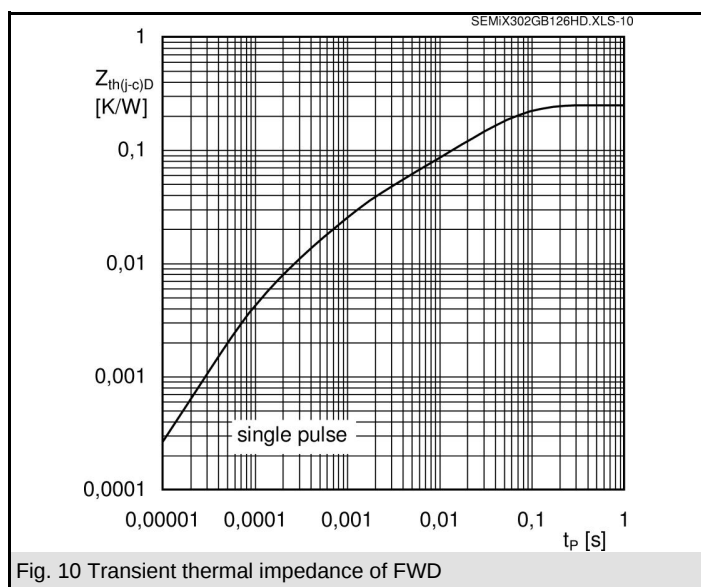
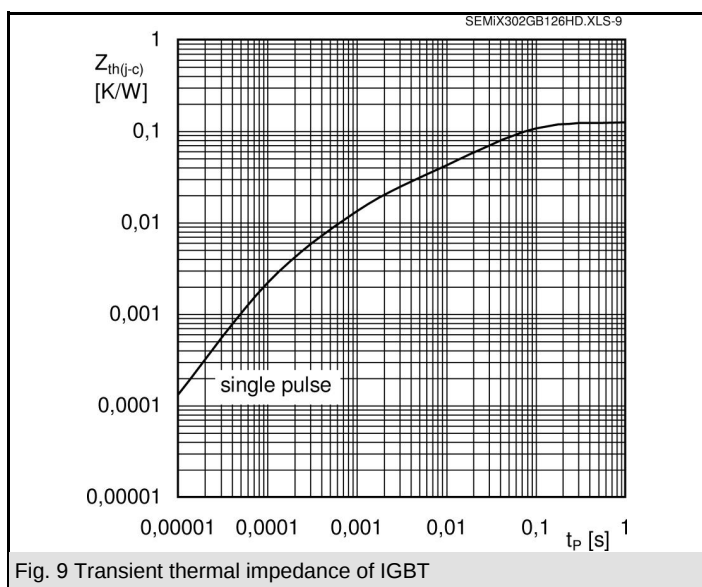
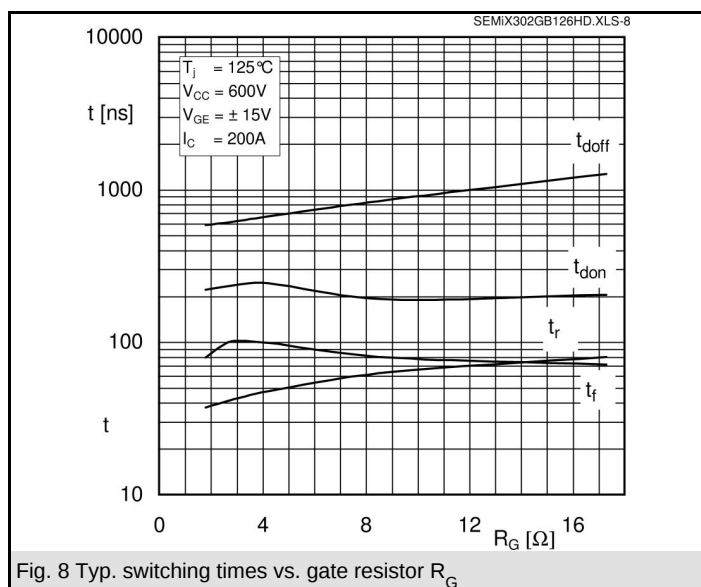
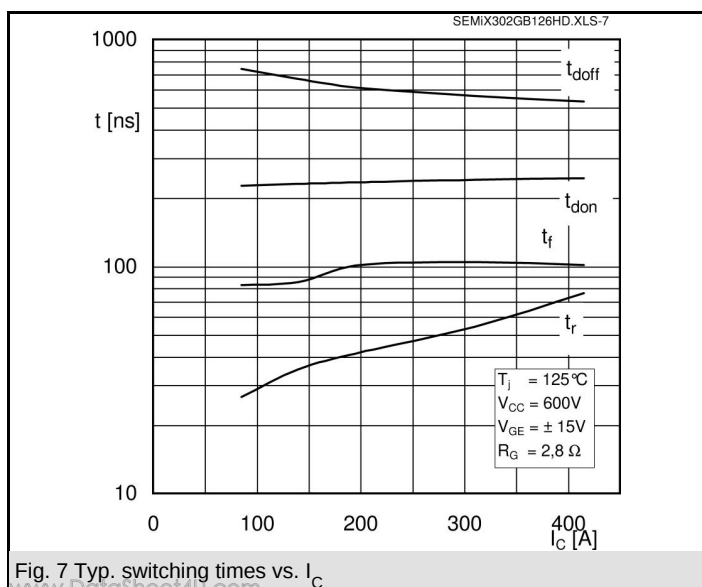
- AC inverter drives
- UPS
- Electronic welders

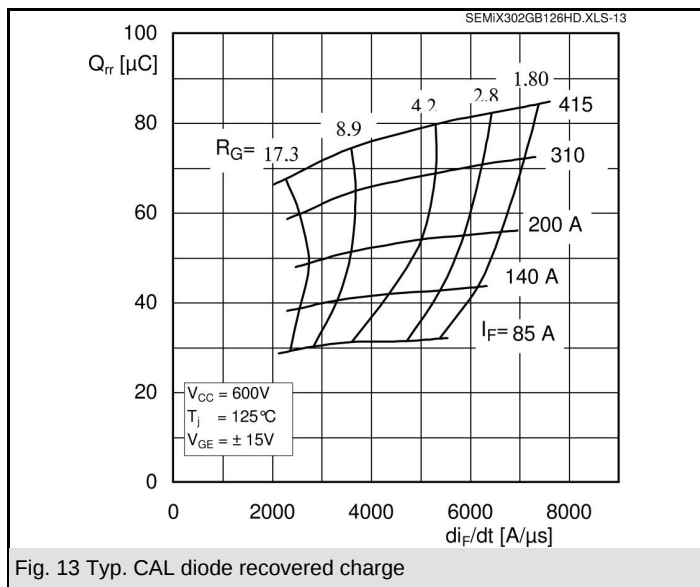
Absolute Maximum Ratings		$T_{case} = 25^{\circ}C$, unless otherwise specified	
Symbol	Conditions	Values	Units
IGBT			
V_{CES}		1200	V
I_C	$T_c = 25 (80)^{\circ}C$	300 (210)	A
I_{CRM}	$t_p = 1 \text{ ms}$	400	A
V_{GES}		± 20	V
T_{vj} (T_{stg})	$T_{OPERATION} \leq T_{stg}$	- 40 ... + 150 (125)	$^{\circ}C$
V_{isol}	AC, 1 min.	4000	V
Inverse diode			
I_F	$T_c = 25 (80)^{\circ}C$	250 (170)	A
I_{FRM}	$t_p = 1 \text{ ms}$	400	A
I_{FSM}	$t_p = 10 \text{ ms}$; sin.; $T_j = 25^{\circ}C$	1300	A

Characteristics		T _{case} = 25 °C, unless otherwise specified			
Symbol	Conditions	min.	typ.	max.	Units
IGBT					
V _{GE(th)}	V _{GE} = V _{CE} , I _C = 8 mA	5	5,8	6,5	V
I _{CES}	V _{GE} = 0, V _{CE} = V _{CES} , T _j = 25 (125) °C			1,3	mA
V _{CE(TO)}	T _j = 25 (125) °C		1 (0,9)	1,2 (1,1)	V
r _{CE}	V _{GE} = 15 V, T _j = 25 (125) °C		3,5 (5,5)	4,8 (6,8)	mΩ
V _{CE(sat)}	I _{Cnom} = 200 A, V _{GE} = 15 V, T _j = 25 (125) °C, chip level		1,7 (2)	2,15 (2,45)	V
C _{ies}	under following conditions		14,4		nF
C _{oes}	V _{GE} = 0, V _{CE} = 25 V, f = 1 MHz		0,8		nF
C _{res}			0,7		nF
L _{CE}			18		nH
R _{CC'+EE'}	terminal-chip, T _c = 25 (125) °C				mΩ
t _{d(on)} /t _r	V _{CC} = 600 V, I _{Cnom} = 200 A		320 / 50		ns
t _{d(off)} /t _f	V _{GE} = ± 15 V		600 / 100		ns
E _{on} (E _{off})	R _{Gon} = R _{Goff} = 2,8 Ω, T _j = 125 °C		30 (26)		mJ
Inverse diode					
V _F = V _{EC}	I _{Fnom} = 200 A; V _{GE} = 0 V; T _j = 25 (125) °C, chip level		1,6 (1,6)	1,8 (1,8)	V
V _(TO)	T _j = 25 (125) °C		1 (0,8)	1,1 (0,9)	V
r _T	T _j = 25 (125) °C		3 (4)	3,5 (4,5)	mΩ
I _{RRM}	I _{Fnom} = 200 A; T _j = 25 (125) °C		(290)		A
Q _{rr}	di/dt = 5900 A/μs		(55)		μC
E _{rr}	V _{GE} = -15 V		(22)		mJ
Thermal characteristics					
R _{th(j-c)}	per IGBT			0,125	K/W
R _{th(j-c)D}	per Inverse Diode			0,25	K/W
R _{th(j-c)FD}	per FWD				K/W
R _{th(c-s)}	per module		0,045		K/W
Temperature sensor					
R ₂₅	T _c = 25 °C		5 ±5%		kΩ
B _{25/85}	R ₂ =R ₁ exp[B(1/T ₂ -1/T ₁)] ; T[K];B		3420		K
Mechanical data					
M _s /M _t	to heatsink (M5) / for terminals (M6)	3/2,5		5 / 5	Nm
w			250		g

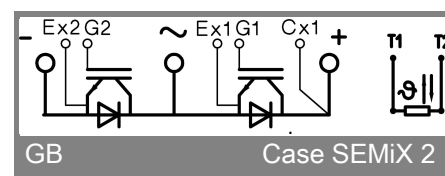
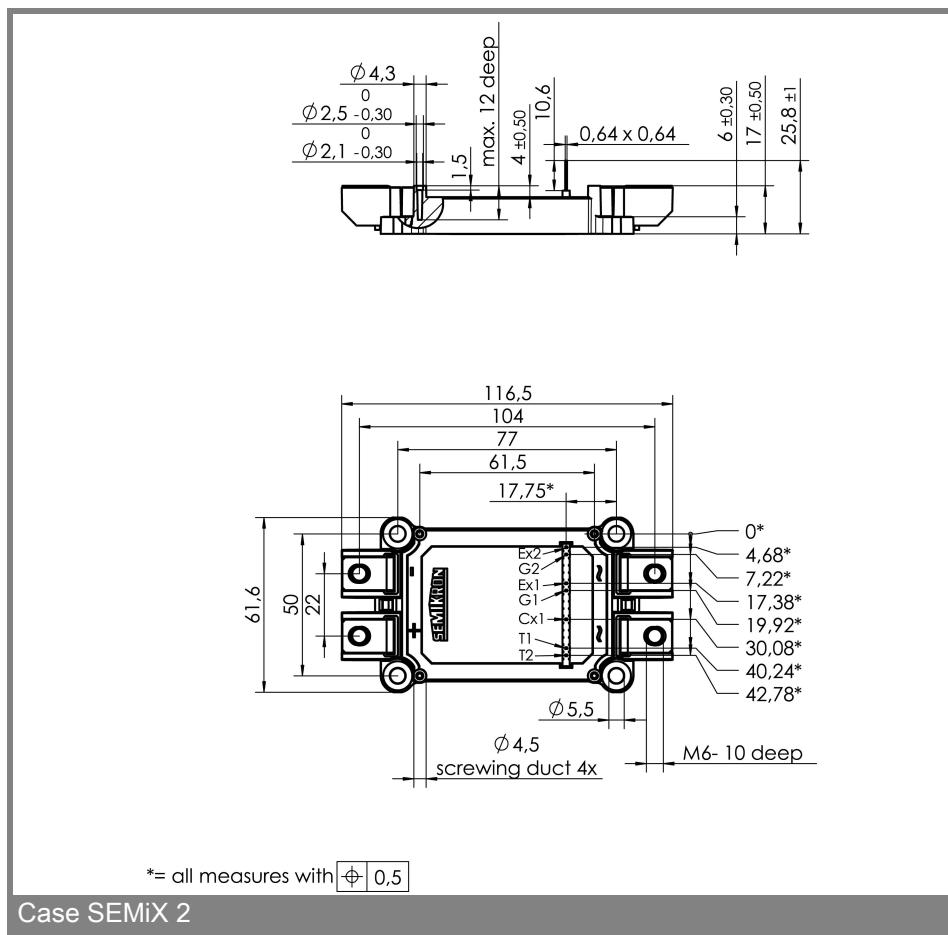








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This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

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